优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

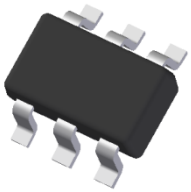
- Epitaxial Planar Die Construction
- Built-In Biasing Resistors
- Surface Mount Package Suited for Automated Assembly

Mechanical Data

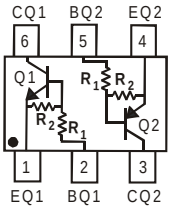
- Case: SOT363
- Case Material: Molded Plastic, “Green” Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.006 grams (Approximate)

R1(NOM)	R2(NOM)
10kΩ	47kΩ

SOT363



Top View



Device Schematic

Absolute Maximum Ratings - NPN Section (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Supply Voltage <Pin: (6) to (1)>	V_{CC}	50	V
Input Voltage <Pin: (2) to (1)>	V_{IN}	-6 to +40	V
Output Current	I_O	70	mA
Output Current	I_C (Max)	100	mA

Absolute Maximum Ratings - PNP Section (@T_A = +25°C, unless otherwise specified.)

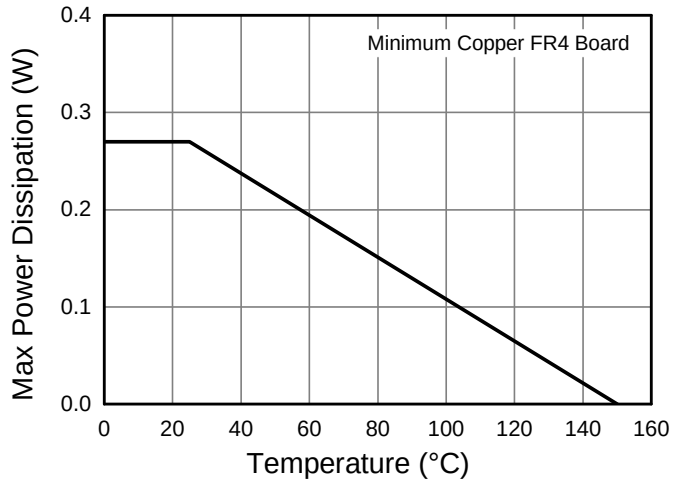
Characteristic	Symbol	Value	Unit
Supply Voltage <Pin: (4) to (3)>	V_{CC}	-50	V
Input Voltage <Pin: (5) to (4)>	V_{IN}	+6 to -40	V
Output Current	I_O	-70	mA
Output Current	I_C (Max)	-100	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

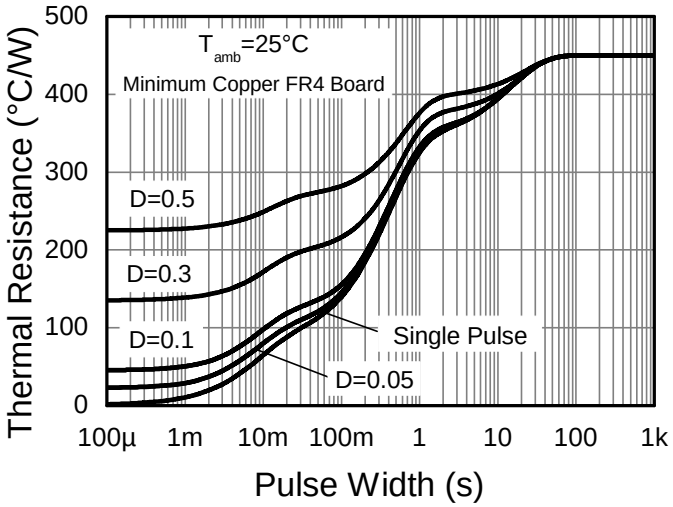
Characteristic	Symbol	Value	Unit
Power Dissipation (Notes 6 & 7)	P_D	270	mW
Thermal Resistance, Junction to Ambient Air (Note 6)	$R_{\theta JA}$	450	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Notes: 6. Mounted on FR4 PC Board with minimum recommended pad layout.
7. 150mW per element must not be exceeded.

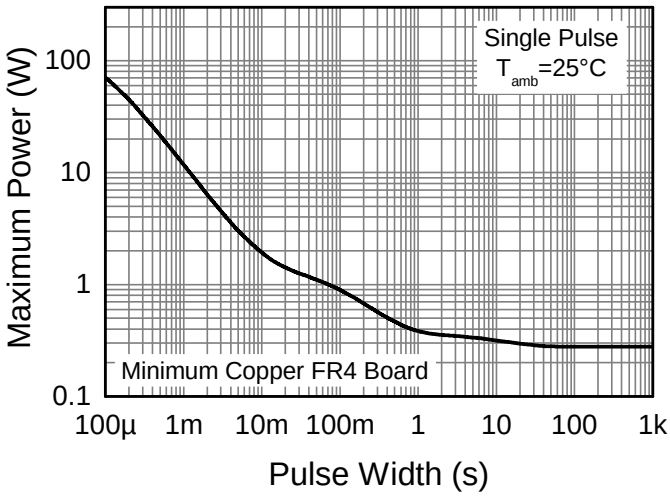
Thermal Characteristics and Derating Information



Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation

Electrical Characteristics - NPN Section (@T_A = +25°C, unless otherwise specified.)

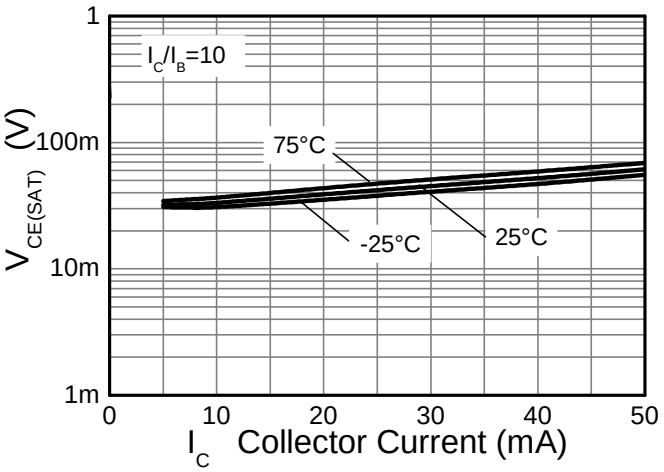
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	$V_{I(OFF)}$	0.3	—	—	V	V_{CC} = 5V, I_O = 100μA
	$V_{I(ON)}$	—	—	1.4		V_O = 0.3V, I_O = 1mA
Output Voltage	$V_{O(ON)}$	—	0.1	0.3	V	I_O/I_I = 5mA / 0.25mA
Input Current	I_I	—	—	0.88	mA	V_I = 5V
Output Current	$I_{O(OFF)}$	—	—	0.5	μA	V_{CC} = 50V, V_I = 0V
DC Current Gain (Note 8)	G_I	80	—	—	—	V_O = 5V, I_O = 10mA
Input Resistor (R_1) Tolerance	ΔR_1	-30	—	+30	%	—
Resistance Ratio Tolerance	$\Delta R_2/R_1$	-20	—	+20	%	—
Gain-Bandwidth Product	f_T	—	250	—	MHz	V_{CE} = 10V, I_E = 5mA, f = 100MHz

Electrical Characteristics - PNP Section (@T_A = +25°C, unless otherwise specified.)

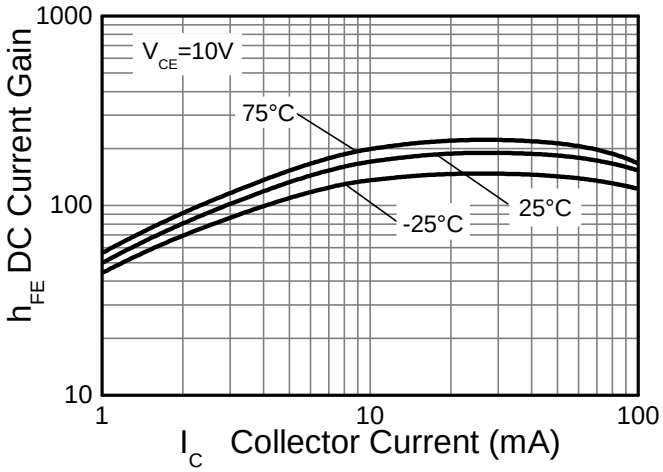
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	$V_{I(OFF)}$	-0.3	—	—	V	V_{CC} = -5V, I_O = -100μA
	$V_{I(ON)}$	—	—	-1.4		V_O = -0.3V, I_O = -1mA
Output Voltage	$V_{O(ON)}$	—	-0.1	-0.3	V	I_O/I_I = -5mA / -0.25mA
Input Current	I_I	—	—	-0.88	mA	V_I = -5V
Output Current	$I_{O(OFF)}$	—	—	-0.5	μA	V_{CC} = -50V, V_I = 0V
DC Current Gain (Note 8)	G_I	80	—	—	—	V_O = -5V, I_O = -10mA
Input Resistor (R_1) Tolerance	ΔR_1	-30	—	+30	%	—
Resistance Ratio Tolerance	$\Delta R_2/R_1$	-20	—	+20	%	—
Gain-Bandwidth Product	f_T	—	250	—	MHz	V_{CE} = -10V, I_E = -5mA, f = 100MHz

Note: 8. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

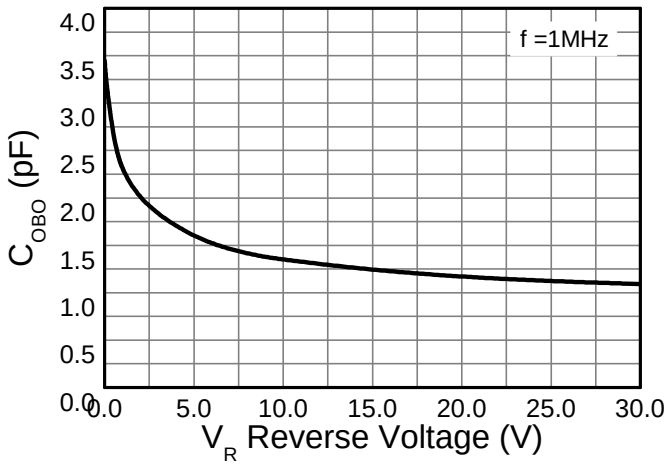
Typical Electrical Characteristics – NPN Section (@T_A = +25°C, unless otherwise specified.)



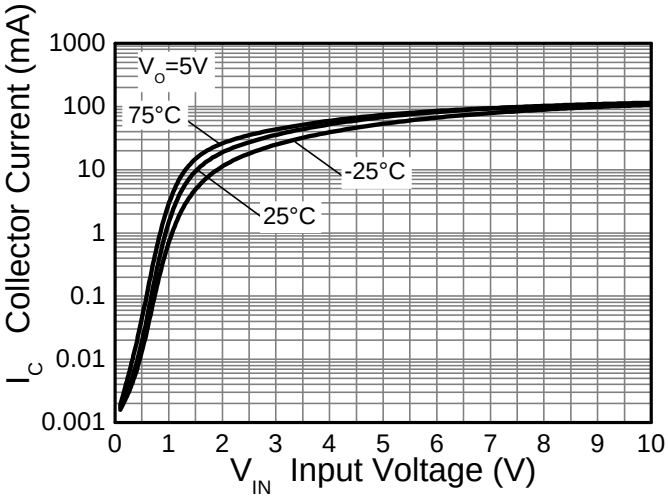
$V_{CE(SAT)}$ v Collector Current



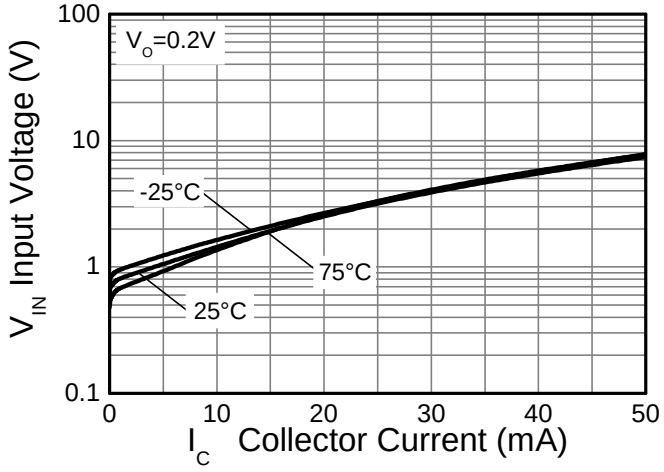
h_{FE} v Collector Current



Output Capacitance

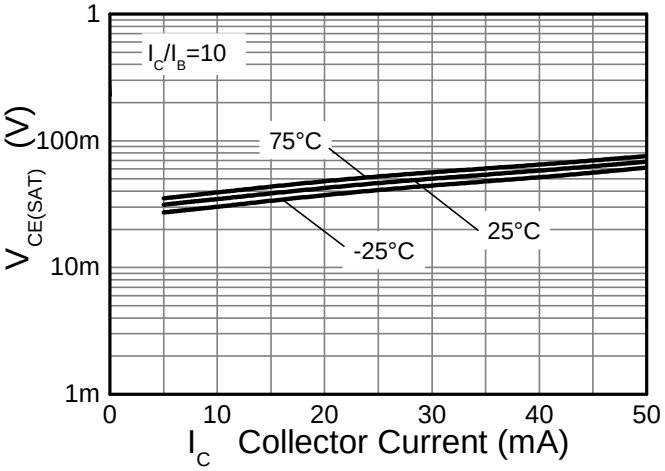


Collector Current v Input Voltage

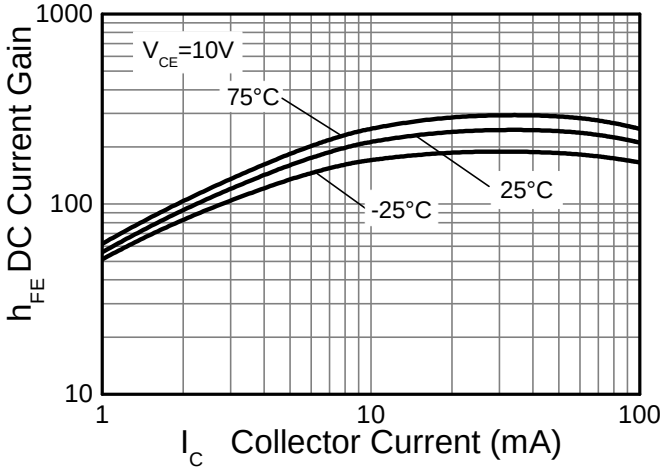


Input Voltage v Collector Current

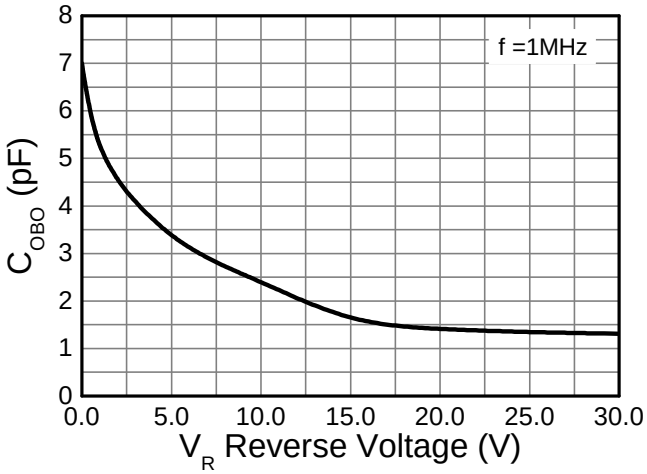
Typical Electrical Characteristics – PNP Section (@T_A = +25°C, unless otherwise specified.)



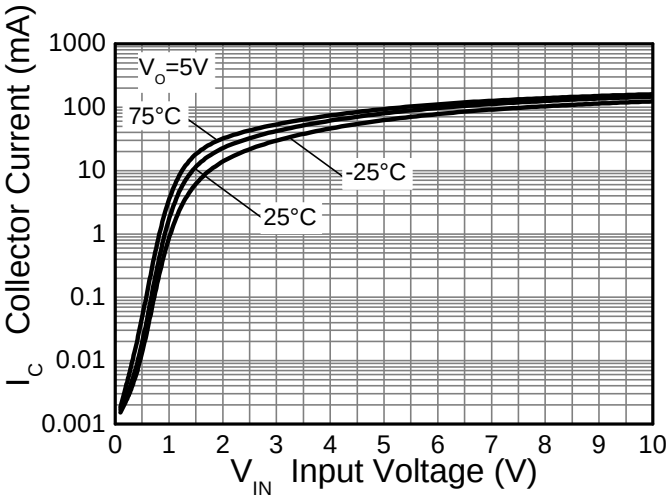
$V_{CE(SAT)}$ v Collector Current



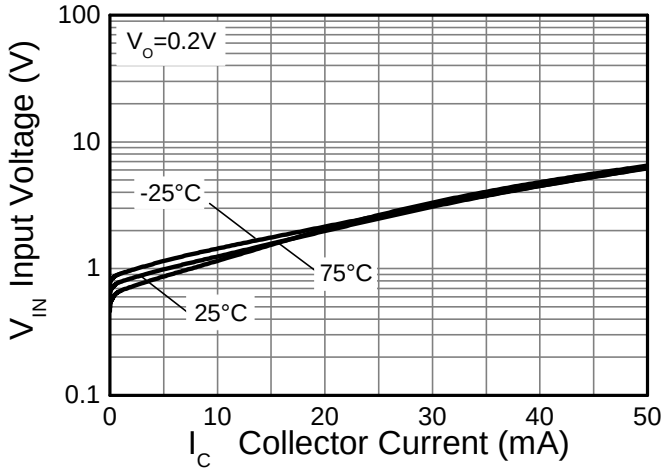
h_{FE} v Collector Current



Output Capacitance

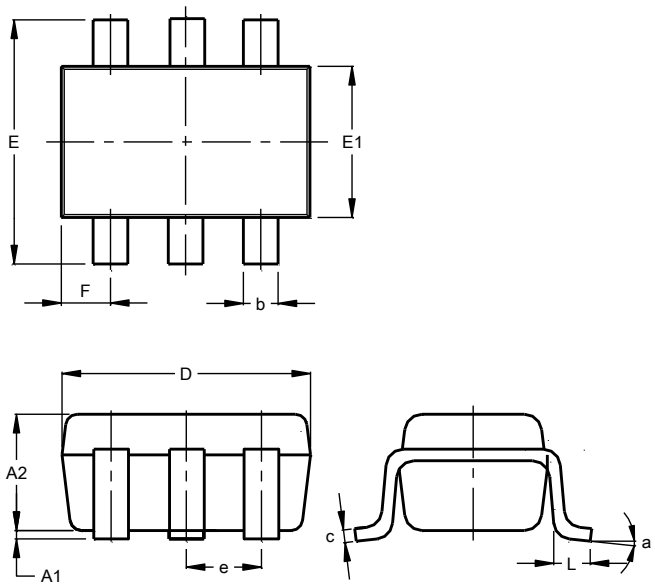


Collector Current v Input Voltage



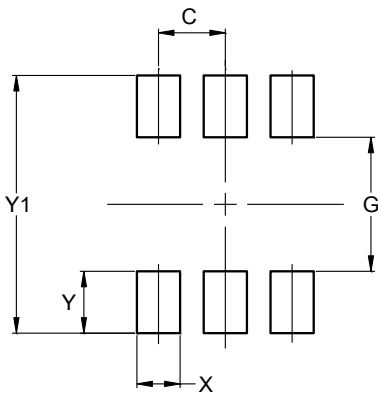
Input Voltage v Collector Current

Package Outline Dimensions



SOT363			
Dim	**Min**	**Max**	**Typ**
A1	0.00	0.10	0.05
A2	0.90	1.00	1.00
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500